

## MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## OptiMOS™

OptiMOS™5 Power-MOSFET, 25 V  
BSC015NE2LS5I

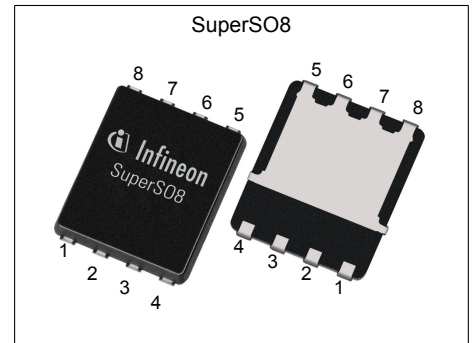
## Data Sheet

Rev. 2.0  
Final

## 1 Description

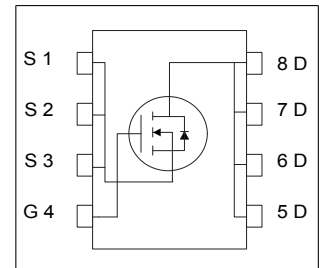
### Features

- Optimized for high performance buck converters
- Monolithic integrated Schottky-like diode
- Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$
- 100% avalanche tested
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit      |
|------------------|-------|-----------|
| $V_{DS}$         | 25    | V         |
| $R_{DS(on),max}$ | 1.5   | $m\Omega$ |
| $I_D$            | 100   | A         |
| $Q_{OSS}$        | 17.5  | nC        |
| $Q_G(0V..4.5V)$  | 10.5  | nC        |



| Type / Ordering Code | Package    | Marking  | Related Links |
|----------------------|------------|----------|---------------|
| BSC015NE2LS5I        | PG-TDSON-8 | 15NE2L5I | -             |

<sup>1)</sup> J-STD20 and JESD22

**Table of Contents**

|   |    |
|---|----|
| Description .....                         | 2  |
| Maximum ratings .....                     | 4  |
| Thermal characteristics .....             | 4  |
| Electrical characteristics .....          | 5  |
| Electrical characteristics diagrams ..... | 7  |
| Package Outlines .....                    | 11 |
| Revision History .....                    | 13 |
| Disclaimer .....                          | 13 |

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                     | Symbol         | Values |      |      | Unit | Note / Test Condition   |
|---|----------------|--------|------|------|------|---|
|   |                | Min.   | Typ. | Max. |      |   |
| Continuous drain current                      | $I_D$          | -      | -    | 100  | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=4.5\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=4.5\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^1)$ |
|   |                | -      | -    | 93   |      |   |
|   |                | -      | -    | 100  |      |   |
|   |                | -      | -    | 78   |      |   |
|   |                | -      | -    | 33   |      |   |
| Pulsed drain current <sup>2)</sup>            | $I_{D,pulse}$  | -      | -    | 400  | A    | $T_C=25\text{ °C}$  |
| Avalanche current, single pulse <sup>3)</sup> | $I_{AS}$       | -      | -    | 50   | A    | $T_C=25\text{ °C}$  |
| Avalanche energy, single pulse                | $E_{AS}$       | -      | -    | 18   | mJ   | $I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$   |
| Gate source voltage                           | $V_{GS}$       | -16    | -    | 16   | V    | -   |
| Power dissipation                             | $P_{tot}$      | -      | -    | 50   | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^1)$  |
|   |                | -      | -    | 2.5  |      |   |
| Operating and storage temperature             | $T_j, T_{stg}$ | -55    | -    | 150  | °C   | IEC climatic category;<br>DIN IEC 68-1: 55/150/56   |

## 3 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter   | Symbol     | Values |      |      | Unit | Note / Test Condition |
|---|------------|--------|------|------|------|-----------------------|
|   |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case, bottom                 | $R_{thJC}$ | -      | -    | 2.5  | K/W  | -                     |
| Thermal resistance, junction - case, top                    | $R_{thJC}$ | -      | -    | 20   | K/W  | -                     |
| Device on PCB, 6 cm <sup>2</sup> cooling area <sup>1)</sup> | $R_{thJA}$ | -      | -    | 50   | K/W  | -                     |

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>2)</sup> See Diagram 3 for more detailed information

<sup>3)</sup> See Diagram 13 for more detailed information

## 4 Electrical characteristics

**Table 4 Static characteristics**

| Parameter                                 | Symbol              | Values |      |      | Unit       | Note / Test Condition   |
|---|---------------------|--------|------|------|------------|---|
|   |                     | Min.   | Typ. | Max. |            |   |
| Drain-source breakdown voltage            | $V_{(BR)DSS}$       | 25     | -    | -    | V          | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$   |
| Breakdown voltage temperature coefficient | $dV_{(BR)DSS}/dT_j$ | -      | 15   | -    | mV/K       | $I_D=10\text{ mA}$ , referenced to 25 °C  |
| Gate threshold voltage                    | $V_{GS(th)}$        | 1.2    | -    | 2    | V          | $V_{DS}=V_{GS}$ , $I_D=250\text{ }\mu\text{A}$  |
| Zero gate voltage drain current           | $I_{DSS}$           | -      | -    | 0.5  | mA         | $V_{DS}=20\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$<br>$V_{DS}=20\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$ |
| Gate-source leakage current               | $I_{GSS}$           | -      | 10   | 100  | nA         | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$  |
| Drain-source on-state resistance          | $R_{DS(on)}$        | -      | 1.7  | 2.2  | m $\Omega$ | $V_{GS}=4.5\text{ V}$ , $I_D=30\text{ A}$<br>$V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$   |
| Gate resistance                           | $R_G$               | -      | 0.85 | 1.4  | $\Omega$   | -   |
| Transconductance                          | $g_{fs}$            | 75     | 150  | -    | S          | $ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=30\text{ A}$  |

**Table 5 Dynamic characteristics**

| Parameter                        | Symbol       | Values |      |      | Unit | Note / Test Condition  |
|----------------------------------|--------------|--------|------|------|------|--|
|                                  |              | Min.   | Typ. | Max. |      |  |
| Input capacitance <sup>1)</sup>  | $C_{iss}$    | -      | 1500 | 2000 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=12\text{ V}$ , $f=1\text{ MHz}$                                      |
| Output capacitance <sup>1)</sup> | $C_{oss}$    | -      | 750  | 1000 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=12\text{ V}$ , $f=1\text{ MHz}$                                      |
| Reverse transfer capacitance     | $C_{rss}$    | -      | 60   | -    | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=12\text{ V}$ , $f=1\text{ MHz}$                                      |
| Turn-on delay time               | $t_{d(on)}$  | -      | 4    | -    | ns   | $V_{DD}=12\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Rise time                        | $t_r$        | -      | 4    | -    | ns   | $V_{DD}=12\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Turn-off delay time              | $t_{d(off)}$ | -      | 19   | -    | ns   | $V_{DD}=12\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Fall time                        | $t_f$        | -      | 3    | -    | ns   | $V_{DD}=12\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |

<sup>1)</sup> Defined by design. Not subject to production test

**Table 6 Gate charge characteristics<sup>1)</sup>**

| Parameter                       | Symbol        | Values |      |      | Unit | Note / Test Condition  |
|---------------------------------|---------------|--------|------|------|------|--|
|                                 |               | Min.   | Typ. | Max. |      |  |
| Gate to source charge           | $Q_{gs}$      | -      | 3.7  | -    | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge at threshold        | $Q_{g(th)}$   | -      | 2.4  | -    | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate to drain charge            | $Q_{gd}$      | -      | 2.3  | -    | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Switching charge                | $Q_{sw}$      | -      | 3.5  | -    | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge total               | $Q_g$         | -      | 10.5 | 14   | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate plateau voltage            | $V_{plateau}$ | -      | 2.4  | -    | V    | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge total <sup>2)</sup> | $Q_g$         | -      | 22   | 30   | nC   | $V_{DD}=12\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate charge total, sync. FET    | $Q_{g(sync)}$ | -      | 9.8  | -    | nC   | $V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }4.5\text{ V}$                    |
| Output charge <sup>2)</sup>     | $Q_{oss}$     | -      | 17.5 | 24   | nC   | $V_{DD}=12\text{ V}$ , $V_{GS}=0\text{ V}$                                   |

**Table 7 Reverse diode**

| Parameter                        | Symbol        | Values |      |      | Unit | Note / Test Condition  |
|----------------------------------|---------------|--------|------|------|------|--|
|                                  |               | Min.   | Typ. | Max. |      |  |
| Diode continuous forward current | $I_S$         | -      | -    | 50   | A    | $T_C=25\text{ °C}$   |
| Diode pulse current              | $I_{S,pulse}$ | -      | -    | 400  | A    | $T_C=25\text{ °C}$   |
| Diode forward voltage            | $V_{SD}$      | -      | 0.5  | 0.65 | V    | $V_{GS}=0\text{ V}$ , $I_F=7\text{ A}$ , $T_j=25\text{ °C}$        |
| Reverse recovery charge          | $Q_{rr}$      | -      | 12   | -    | nC   | $V_R=12\text{ V}$ , $I_F=I_S$ , $di_F/dt=400\text{ A}/\mu\text{s}$ |

<sup>1)</sup> See "Gate charge waveforms" for parameter definition

<sup>2)</sup> Defined by design. Not subject to production test

## 5 Electrical characteristics diagrams

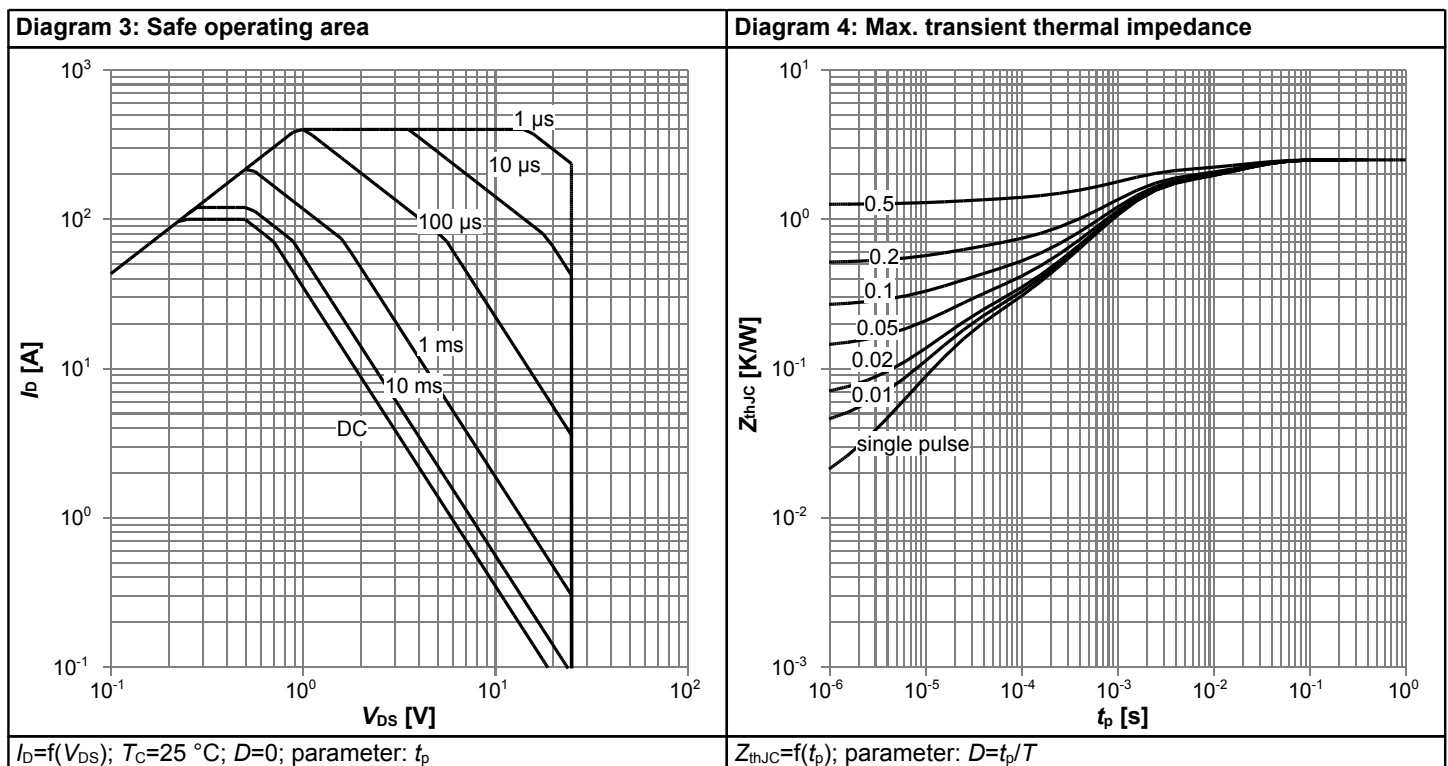
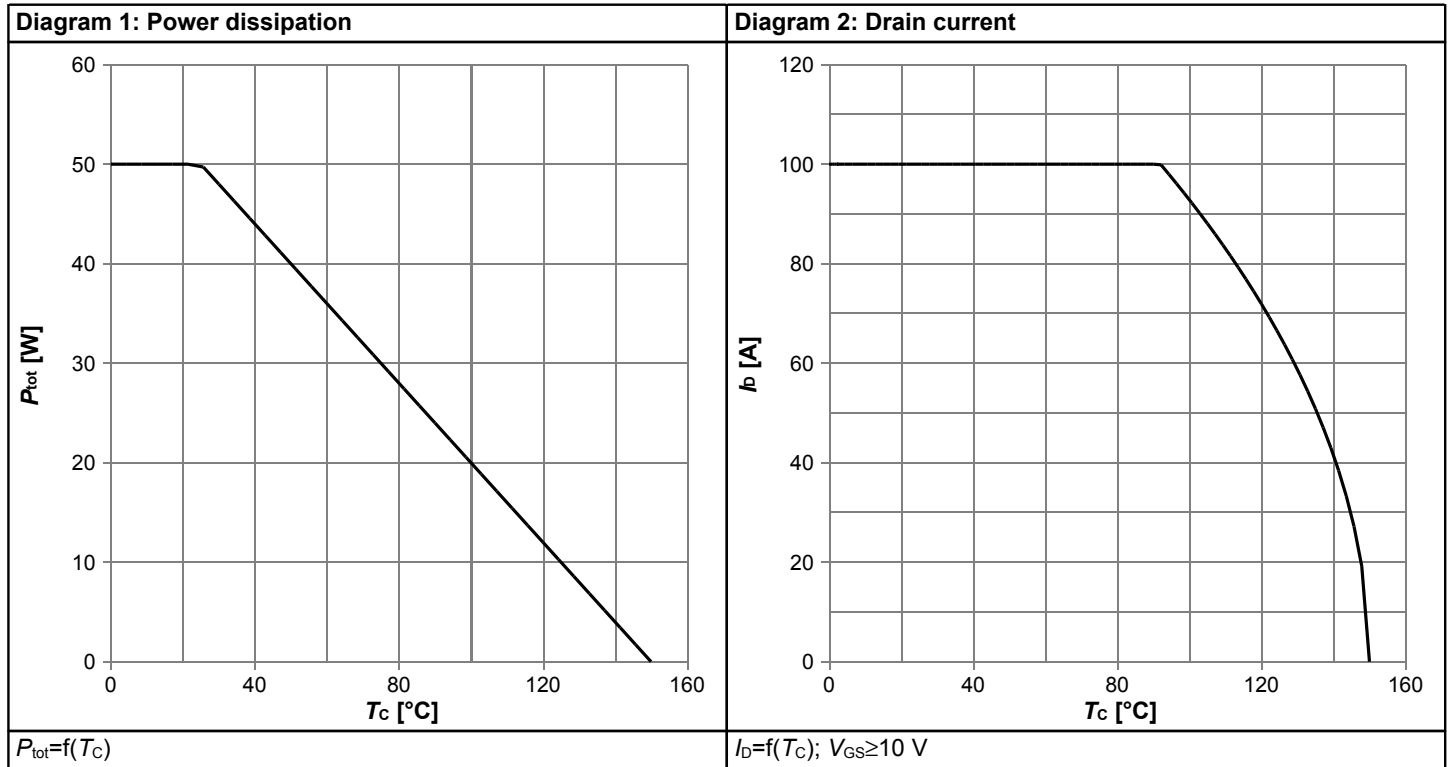
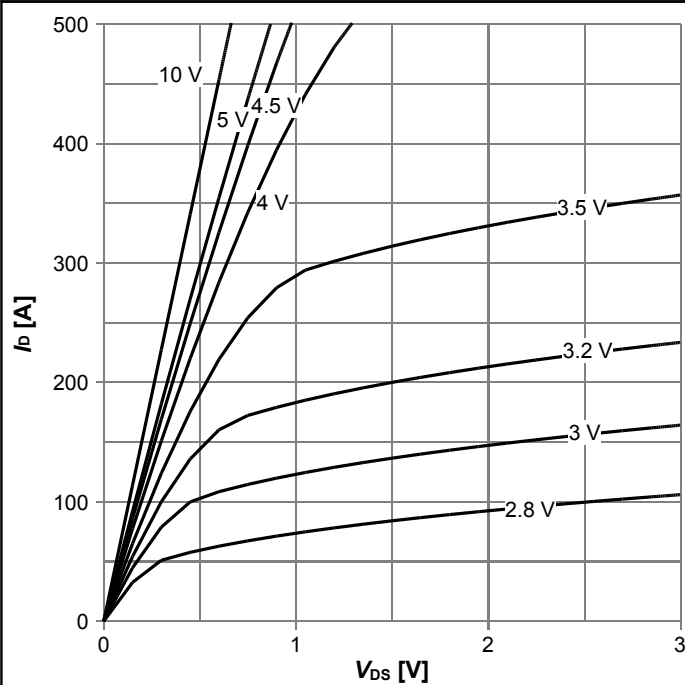
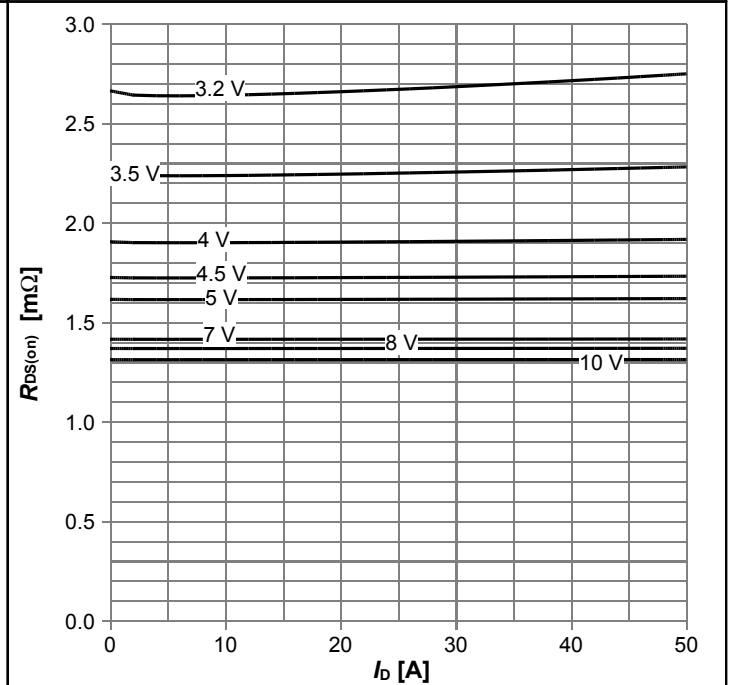


Diagram 5: Typ. output characteristics



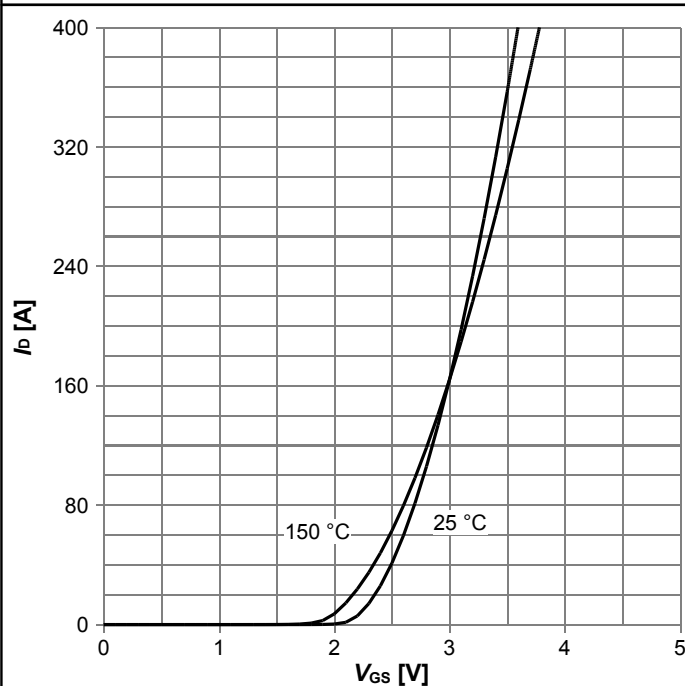
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



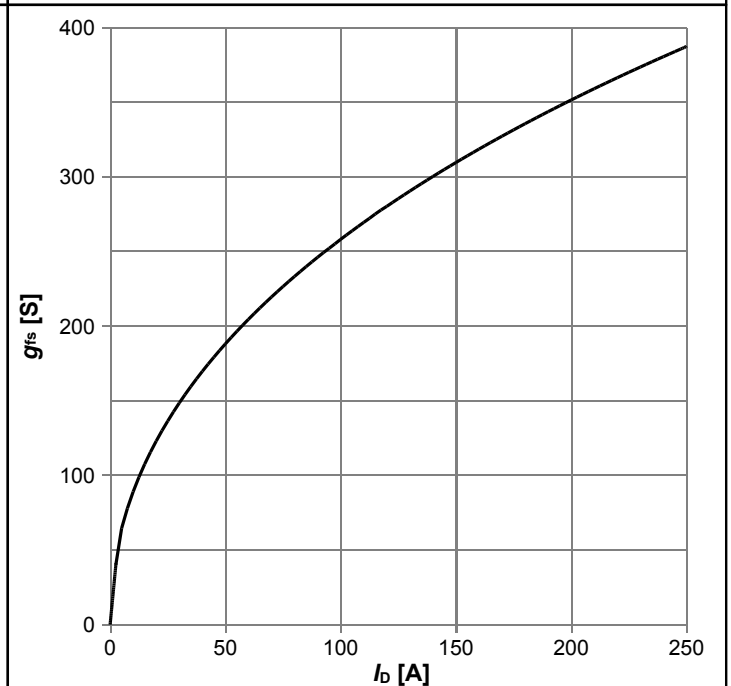
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max};$  parameter:  $T_j$

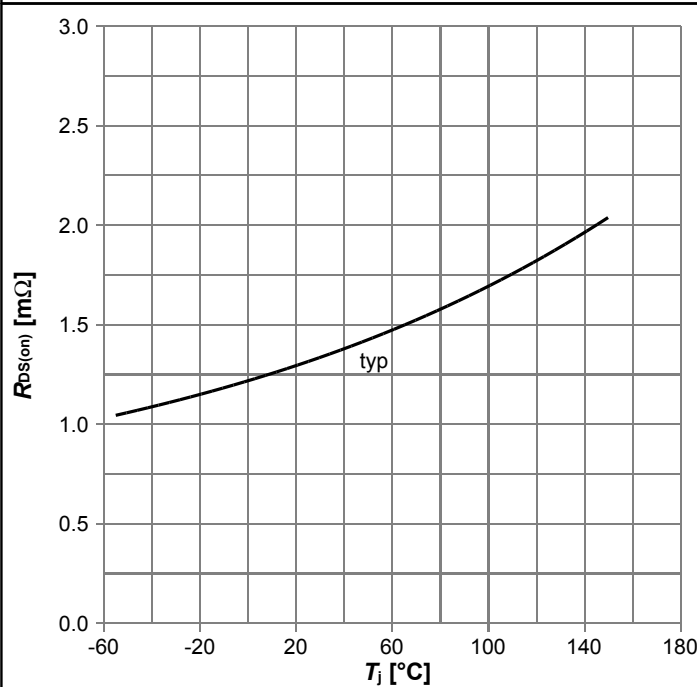
Diagram 8: Typ. forward transconductance



$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$

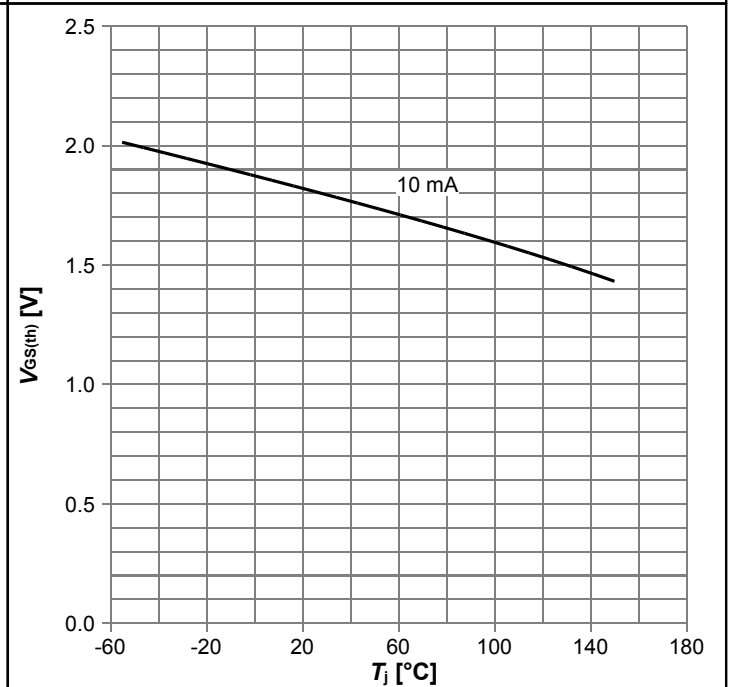


Diagram 9: Drain-source on-state resistance



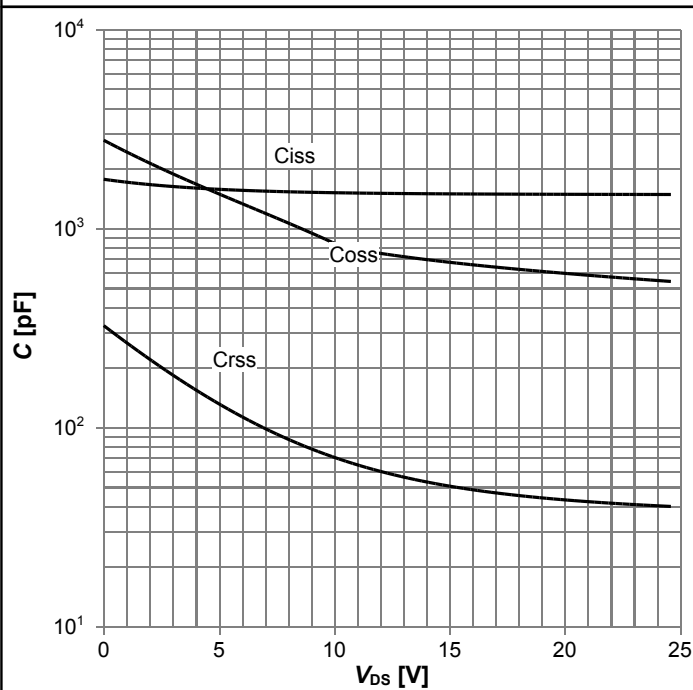
$R_{DS(on)}=f(T_j)$ ;  $I_D=30$  A;  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



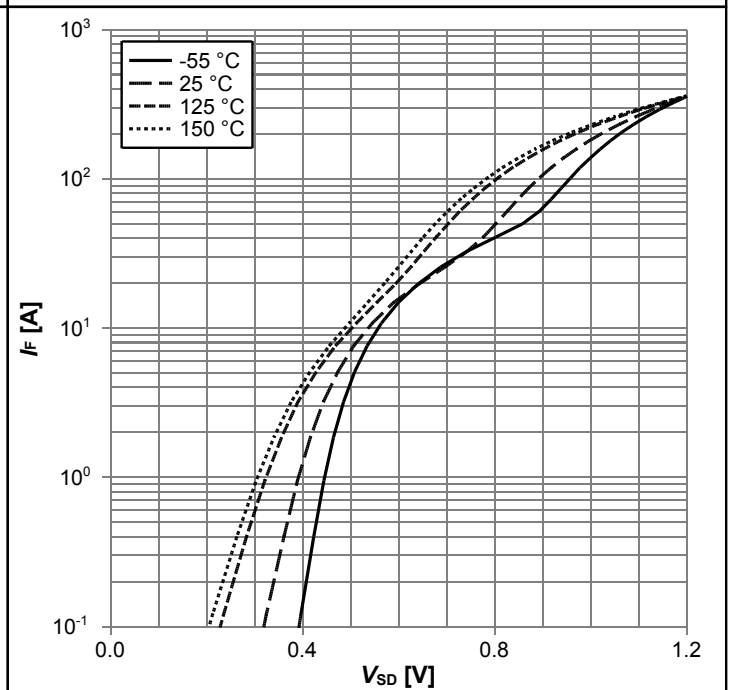
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



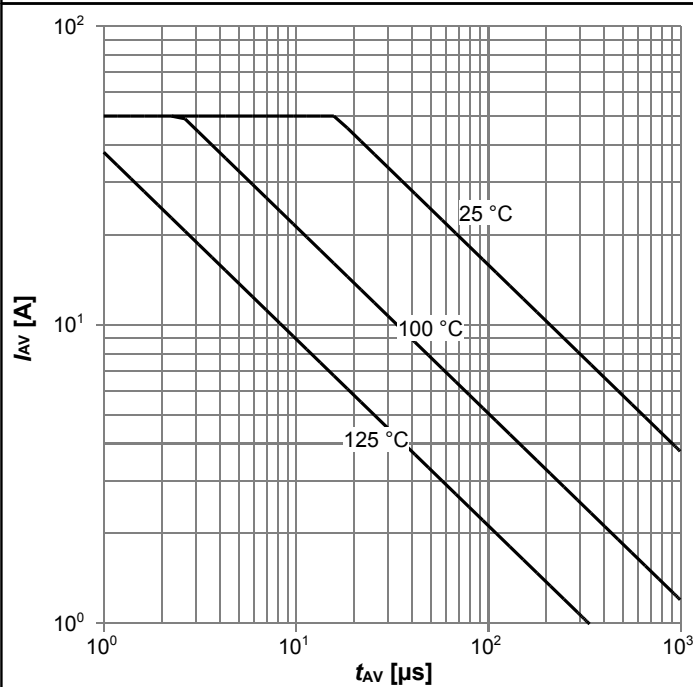
$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

Diagram 12: Forward characteristics of reverse diode



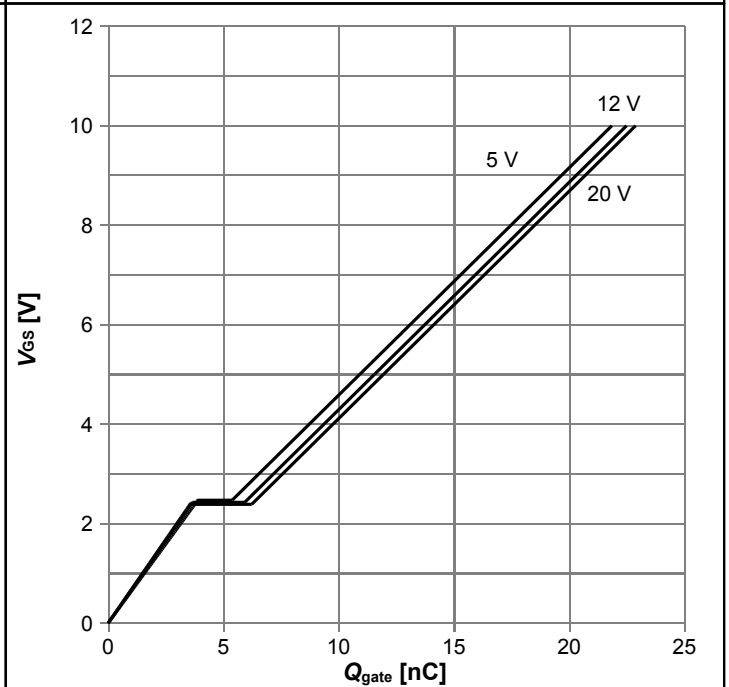
$I_F=f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics



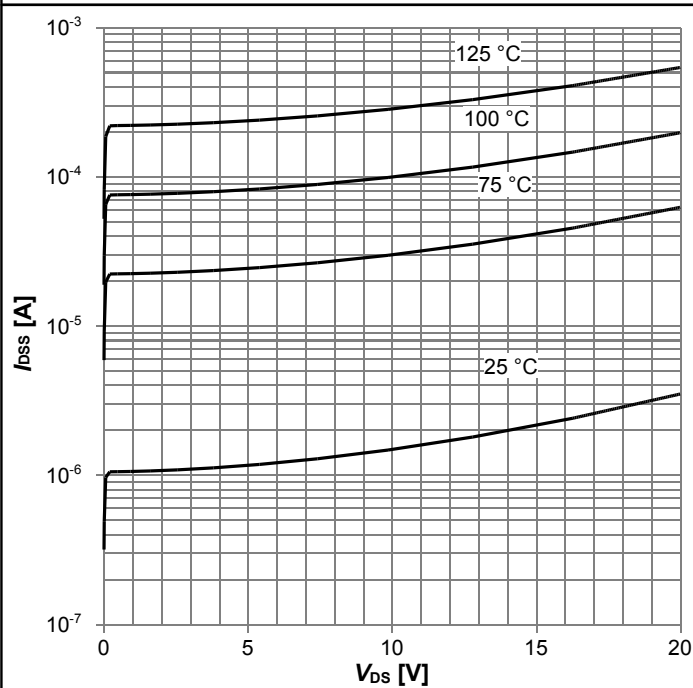
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



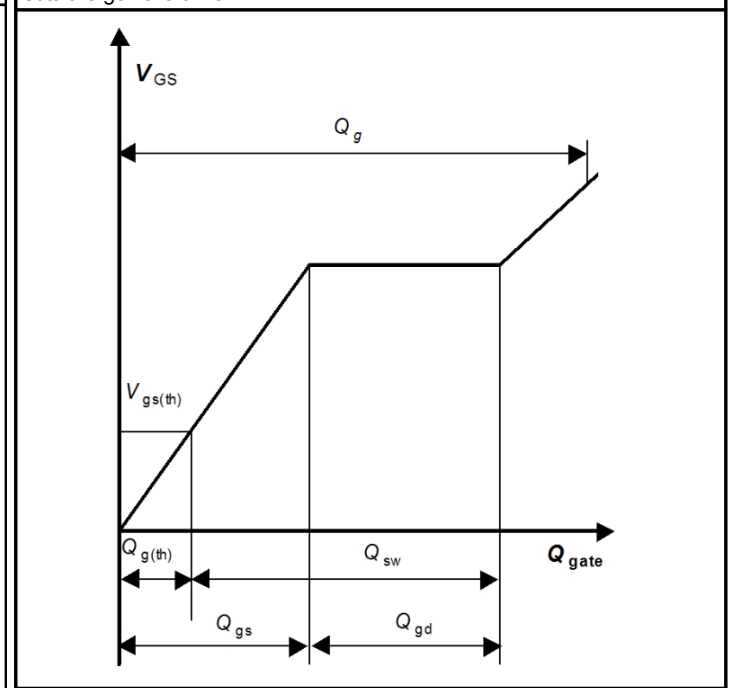
$V_{GS}=f(Q_{gate}); I_D=30 \text{ A}$  pulsed; parameter:  $V_{DD}$

Diagram 15: Typ. drain-source leakage current

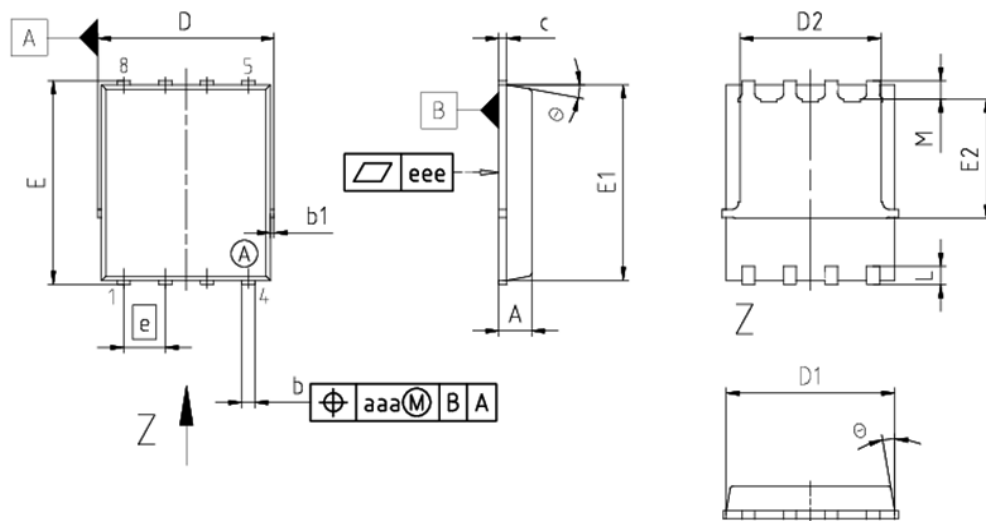


$I_{DSS}=f(V_{DS}); V_{GS}=0 \text{ V}$ ; parameter:  $T_j$

Gate charge waveforms



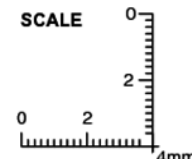
## 6 Package Outlines



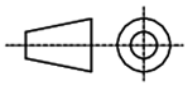
| DIM | MILLIMETERS |      |
|-----|-------------|------|
|     | MIN         | MAX  |
| A   | 0.90        | 1.10 |
| b   | 0.31        | 0.54 |
| b1  | 0.02        | 0.22 |
| c   | 0.15        | 0.35 |
| D   | 5.15        | 5.49 |
| D1  | 4.95        | 5.35 |
| D2  | 3.70        | 4.40 |
| E   | 5.95        | 6.35 |
| E1  | 5.70        | 6.10 |
| E2  | 3.40        | 3.80 |
| e   | 1.27        |      |
| N   | 8           |      |
| L   | 0.45        | 0.71 |
| M   | 0.45        | 0.75 |
| ø   | 8.5°        | 12°  |
| aaa | 0.25        |      |
| eee | 0.08        |      |

**DOCUMENT NO.**  
Z8B00003332

**SCALE**



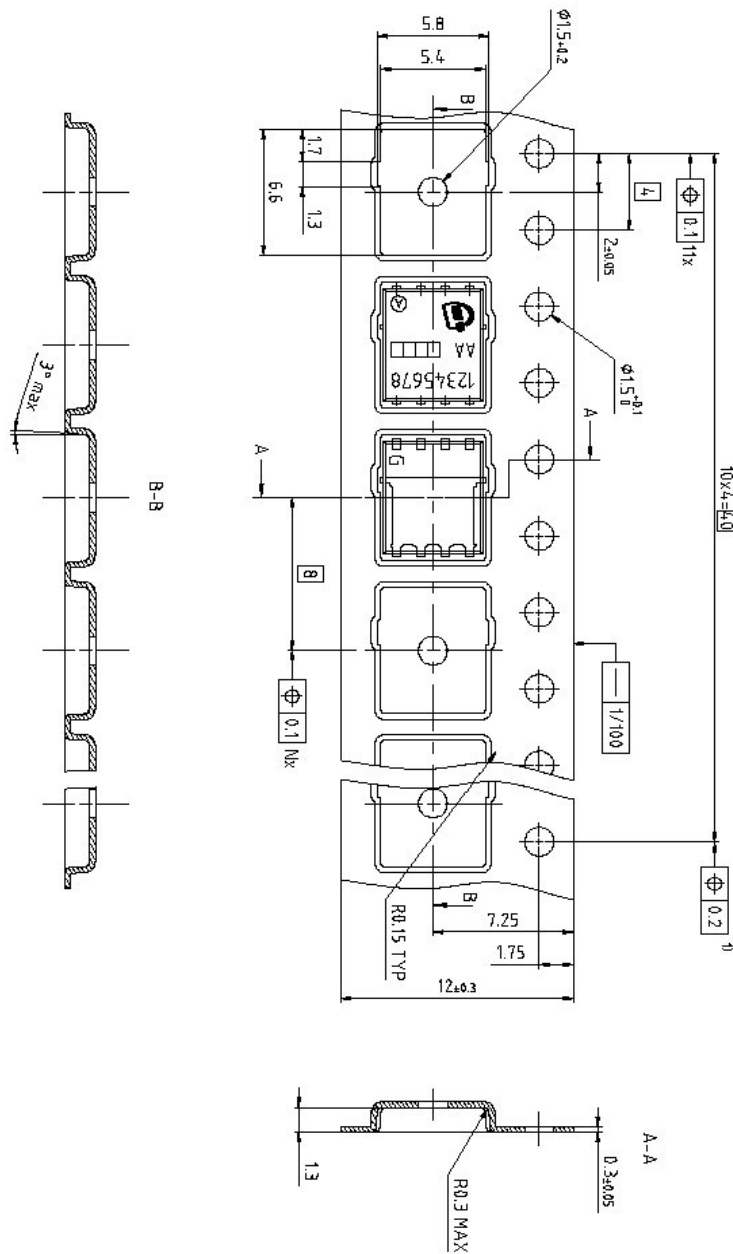
**EUROPEAN PROJECTION**



**ISSUE DATE**  
10-04-2013

**REVISION**  
04

Figure 1 Outline PG-TDSON-8, dimensions in mm



Dimension in mm

Figure 2 Outline TDSON-8 Tape

## Revision History

BSC015NE2LS5I

**Revision: 2015-08-06, Rev. 2.0**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0      | 2015-08-06 | Release of final version                     |

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